

ST1280C..K SERIES

PHASE CONTROL THYRISTORS

Hockey Puk Version

Features

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case A-24 (K-PUK)
- High profile hockey-puk

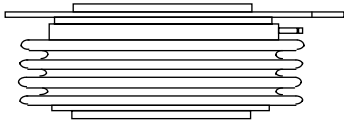
Typical Applications

- DC motor controls
- Controlled DC power supplies
- AC controllers

Major Ratings and Characteristics

Parameters	ST1280C..K	Units
$I_{T(AV)}$	2310	A
@ T_{hs}	55	°C
$I_{T(RMS)}$	4150	A
@ T_{hs}	25	°C
I_{TSM}	@ 50Hz	42500
	@ 60Hz	44500
I^2t	@ 50Hz	9027
	@ 60Hz	8240
V_{DRM}/V_{RRM}	400 to 600	V
t_q	typical	200
		μs
T_J	- 40 to 125	°C

2310A



case style A-24 (K-PUK)

ST1280C..K Series

Bulletin I25195 rev. B 02/00

International
IR Rectifier

ELECTRICAL SPECIFICATIONS

Voltage Ratings

Type number	Voltage Code	V_{DRM}/V_{RRM} , max. repetitive peak and off-state voltage V	V_{RSM} , maximum non-repetitive peak voltage V	I_{DRM}/I_{RRM} max. @ $T_J = T_J \text{ max}$ mA
ST1280C..K	04	400	500	100
	06	600	700	

On-state Conduction

Parameter	ST1280C..K	Units	Conditions
$I_{T(AV)}$ Max. average on-state current @ Heatsink temperature	2310 (885) 55 (85)	A °C	180° conduction, half sine wave double side (single side) cooled
$I_{T(RMS)}$ Max. RMS on-state current	4150	A	@ 25°C heatsink temperature double side cooled
I_{TSM} Max. peak, one-cycle non-repetitive surge current	42500		t = 10ms No voltage
	44500		t = 8.3ms reapplied
	35700		t = 10ms 100% V_{RRM}
	37400		t = 8.3ms reapplied
I^2t Maximum I^2t for fusing	9027	KA ² s	t = 10ms No voltage
	8241		t = 8.3ms reapplied
	6383		t = 10ms 100% V_{RRM}
	5828		t = 8.3ms reapplied
$I^2\sqrt{t}$ Maximum $I^2\sqrt{t}$ for fusing	90270	KA ² √s	t = 0.1 to 10ms, no voltage reapplied
$V_{T(TO)1}$ Low level value of threshold voltage	0.83	V	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}), T_J = T_J \text{ max.}$
$V_{T(TO)2}$ High level value of threshold voltage	0.90		$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ max.}$
r_{t1} Low level value of on-state slope resistance	0.077	mΩ	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}), T_J = T_J \text{ max.}$
r_{t2} High level value of on-state slope resistance	0.068		$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ max.}$
V_{TM} Max. on-state voltage	1.44	V	$I_{pk} = 8000A, T_J = T_J \text{ max, } t_p = 10ms \text{ sine pulse}$
I_H Maximum holding current	600	mA	$T_J = 25^\circ C$, anode supply 12V resistive load
I_L Typical latching current	1000		

Switching

Parameter	ST1280C..K	Units	Conditions
di/dt Max. non-repetitive rate of rise of turned-on current	1000	A/μs	Gate drive 20V, 20Ω, $t_r \leq 1\mu s$ $T_J = T_J \text{ max, anode voltage} \leq 80\% V_{DRM}$
t_d Typical delay time	1.9	μs	Gate current 1A, $di/dt = 1A/\mu s$ $V_d = 0.67\% V_{DRM}, T_J = 25^\circ C$
t_q Typical turn-off time	200		$I_{TM} = 550A, T_J = T_J \text{ max, } di/dt = 40A/\mu s, V_R = 50V$ $dv/dt = 20V/\mu s, \text{ Gate } 0V \text{ } 100\Omega, t_p = 500\mu s$

Blocking

Parameter	ST1280C..K	Units	Conditions
dv/dt Maximum critical rate of rise of off-state voltage	500	V/ μ s	$T_J = T_J$ max. linear to 80% rated V_{DRM}
I_{RRM} I_{DRM} Max. peak reverse and off-state leakage current	100	mA	$T_J = T_J$ max, rated V_{DRM}/V_{RRM} applied

Triggering

Parameter		ST1280C..K		Units	Conditions
P _{GM}	Maximum peak gate power	16		W	T _J = T _J max, t _p ≤ 5ms
P _{G(AV)}	Maximum average gate power	3			T _J = T _J max, f = 50Hz, d% = 50
I _{GM}	Max. peak positive gate current	3.0		A	T _J = T _J max, t _p ≤ 5ms
+V _{GM}	Maximum peak positive gate voltage	20		V	T _J = T _J max, t _p ≤ 5ms
-V _{GM}	Maximum peak negative gate voltage	5.0			
I _{GT}	DC gate current required to trigger	TYP.	MAX.	mA	T _J = - 40°C T _J = 25°C T _J = 125°C Max. required gate trigger/ current/ voltage are the lowest value which will trigger all units 12V anode-to-cathode applied
		200	-		
		100	200		
		50	-		
V _{GT}	DC gate voltage required to trigger	1.4	-	V	T _J = - 40°C T _J = 25°C T _J = 125°C
		1.1	3.0		
		0.9	-		
I _{GD}	DC gate current not to trigger	10		mA	T _J = T _J max Max. gate current/voltage not to trigger is the max. value which will not trigger any unit with rated V _{DRM} anode-to-cathode applied
V _{GD}	DC gate voltage not to trigger	0.25		V	

Thermal and Mechanical Specification

Parameter	ST1280C..K	Units	Conditions
T_J Max. operating temperature range	-40 to 125	$^\circ\text{C}$	
T_{stg} Max. storage temperature range	-40 to 150		
R_{thJ-hs} Max. thermal resistance, junction to heatsink	0.042 0.021	K/W	DC operation single side cooled DC operation double side cooled
R_{thC-hs} Max. thermal resistance, case to heatsink	0.006 0.003	K/W	DC operation single side cooled DC operation double side cooled
F Mounting force, $\pm 10\%$	24500 (2500)	N (Kg)	
wt Approximate weight	425	g	
Case style	A-24 (K-PUK)		See Outline Table

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ΔR_{thJ-hs} Conduction

(The following table shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC)

Conduction angle	Sinusoidal conduction		Rectangular conduction		Units	Conditions
	Single Side	Double Side	Single Side	Double Side		
180°	0.003	0.003	0.002	0.002	K/W	$T_J = T_{J \text{ max.}}$
120°	0.004	0.004	0.004	0.004		
90°	0.005	0.005	0.005	0.005		
60°	0.007	0.007	0.007	0.007		
30°	0.012	0.012	0.012	0.012		

Ordering Information Table

Device Code

ST1280C06K1

1

2

3

4

5

6

7

8

1

-

Thyristor

2

-

Essential part number

3

-

0 = Converter grade

4

-

C = Ceramic Puk

5

-

Voltage code: Code x 100 = V_{RRM} (See Voltage Rating Table)

6

-

K = Puk Case A-24(K-PUK)

7

-

0 = Eyelet terminals (Gate and Auxiliary Cathode Unsoldered Leads)
1 = Fast-on terminals (Gate and Auxiliary Cathode Unsoldered Leads)
2 = Eyelet terminals (Gate and Auxiliary Cathode Soldered Leads)
3 = Fast-on terminals (Gate and Auxiliary Cathode Soldered Leads)

8

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Critical dv/dt: None = 500V/ μ sec (Standard selection)
L = 1000V/ μ sec (Special selection)

Outline Table

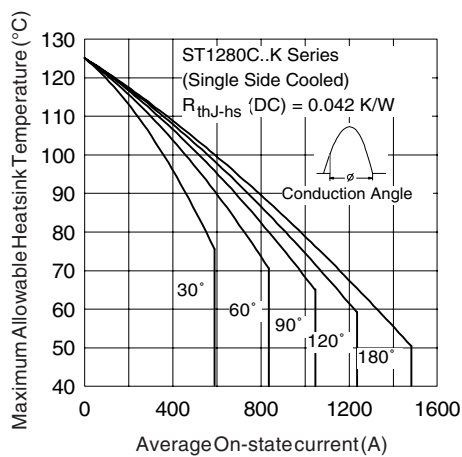
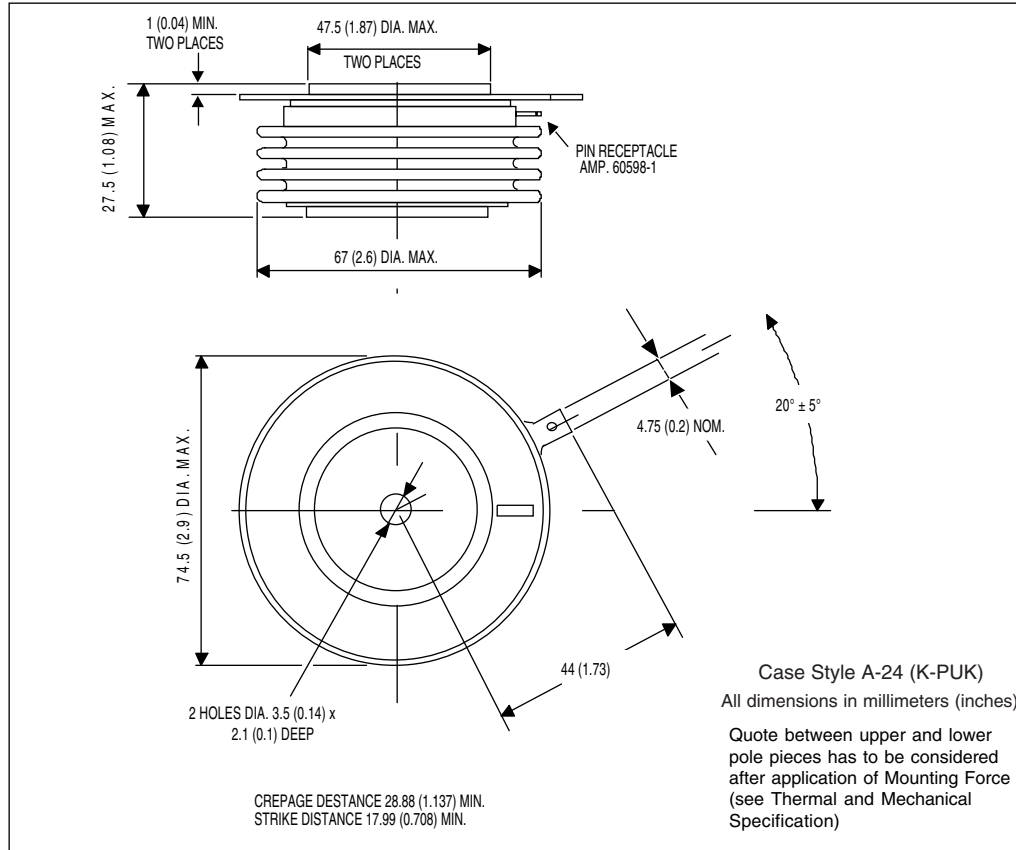


Fig. 1 - Current Ratings Characteristics

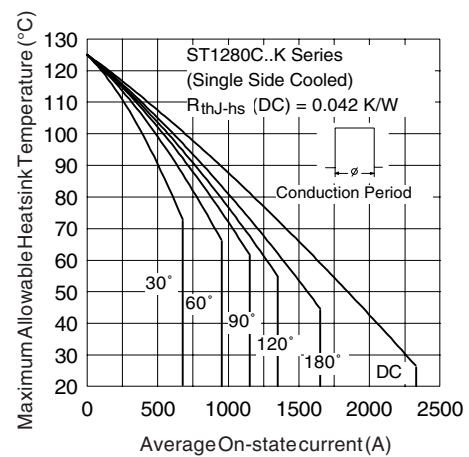


Fig. 2 - Current Ratings Characteristics

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International
IOR Rectifier

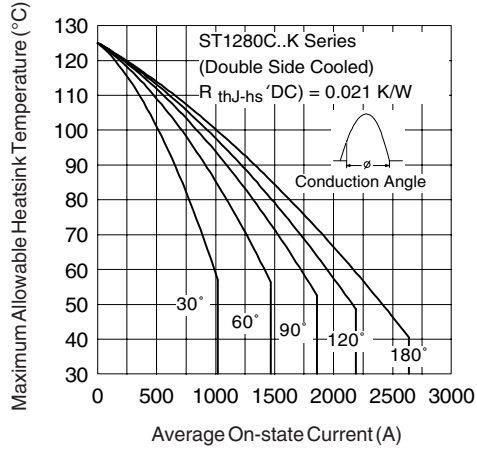


Fig. 3 - Current Ratings Characteristics

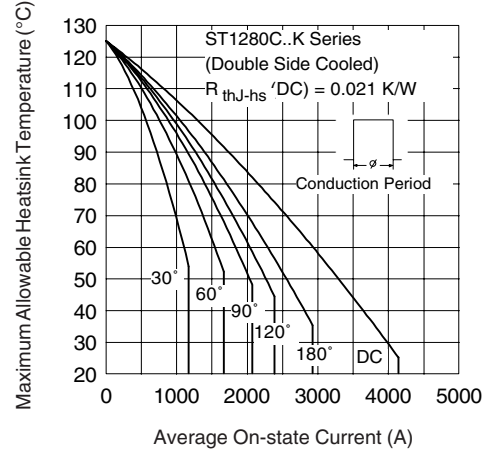


Fig. 4 - Current Ratings Characteristics

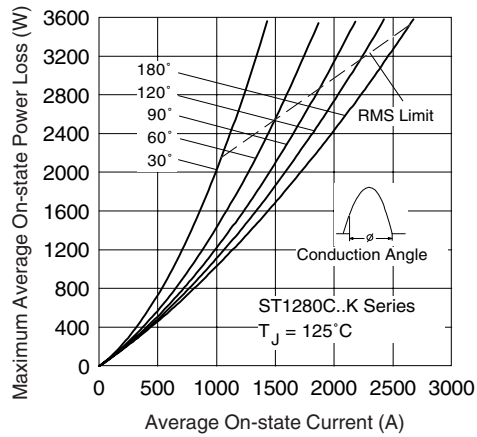


Fig. 5 - On-state Power Loss Characteristics

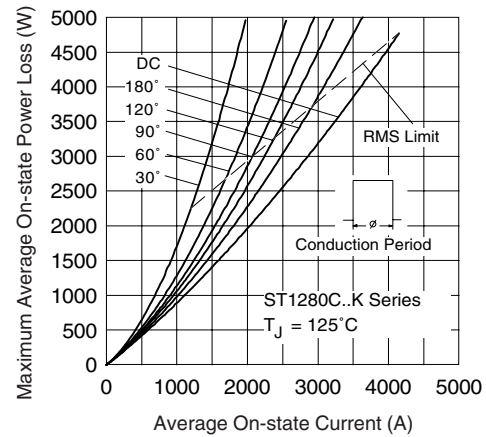


Fig. 6 - On-state Power Loss Characteristics

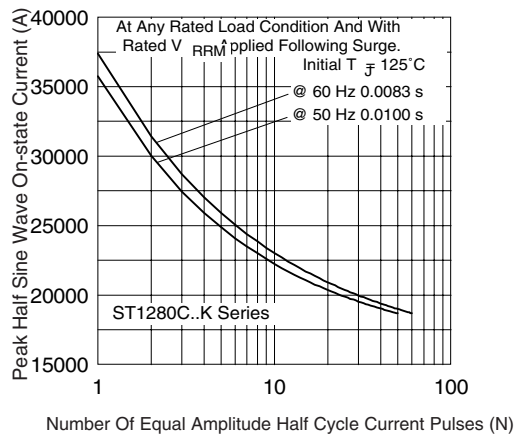


Fig. 7 - Maximum Non-Repetitive Surge Current
Single and Double Side Cooled

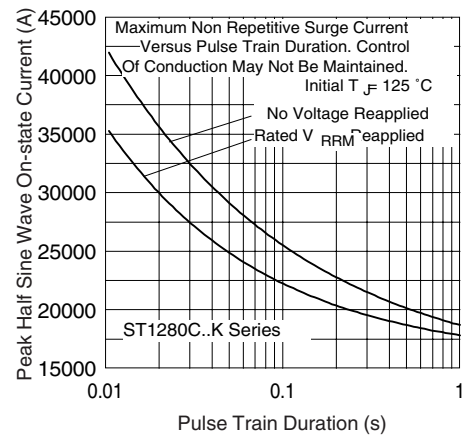


Fig. 8 - Maximum Non-Repetitive Surge Current
Single and Double Side Cooled

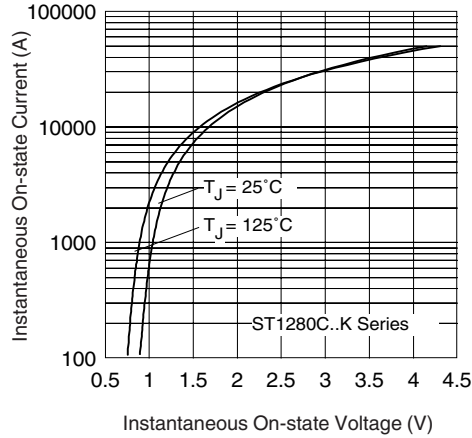


Fig. 9 - On-state Voltage Drop Characteristics

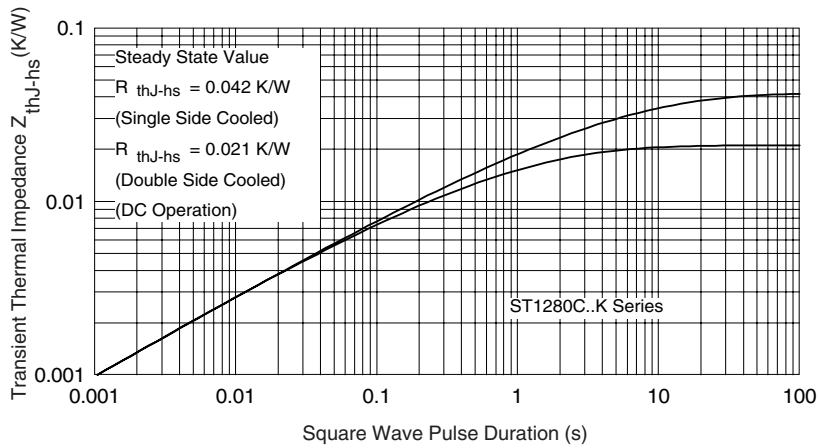


Fig. 10 - Thermal Impedance Z_{thJ-hs} Characteristics

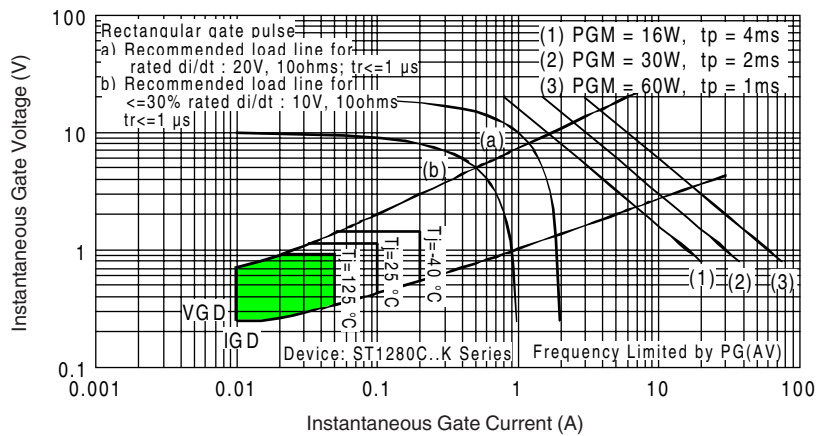


Fig. 11 - Gate Characteristics